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### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Features**

- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free RoHS Compliant (Note 2)
- ESD Protected Up To 2kV
- "Green" Device (Note 4)
- Qualified to AEC-Q101 standards for High Reliability

### **Mechanical Data**

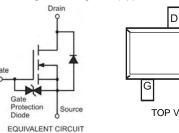
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
  - Weight: 0.006 grams (approximate)

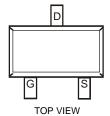




TOP VIEW







**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

ESD protected up to 2kV

Ch	aracteristic	Symbol	Value	Unit	
Drain Source Voltage		$V_{DSS}$	50	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Drain Current (Note 1)	Continuous Pulsed (Note 3)	I <sub>D</sub>	300 800	mA	

# **Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_D$	250	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	500	°C/W
Operating and Storage Temperature Range	$T_J,T_STG$	-65 to +150	°C

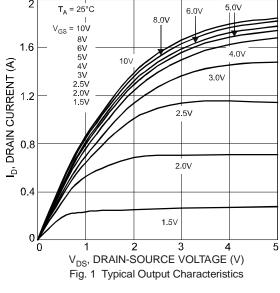
## Electrical Characteristics @TA = 25°C unless otherwise specified

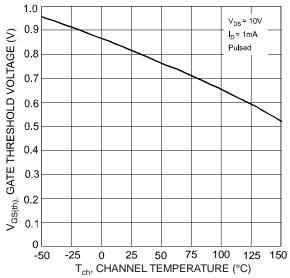
Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage		$BV_{DSS}$	50		_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ $T_C = 25^{\circ}C$	I <sub>DSS</sub>	_	_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
					1	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate-Body Leakage		Igss	_	_	500	nA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$
					50	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)		•		3'			·
Gate Threshold Voltage		V <sub>GS(th)</sub>	0.49	_	1.0	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			_	_	3.0		$V_{GS} = 1.8V, I_D = 50mA$
Static Drain-Source On-Resistance		R <sub>DS</sub> (ON)	_	_	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
			_	_	2.0		$V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current		I <sub>D(ON)</sub>	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		Y <sub>fs</sub>	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage		$V_{SD}$	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS							
Input Capacitance		C <sub>iss</sub>	_	_	50	pF	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance		Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance		$C_{rss}$		_	5.0	pF	71 = 1.01VII 1Z

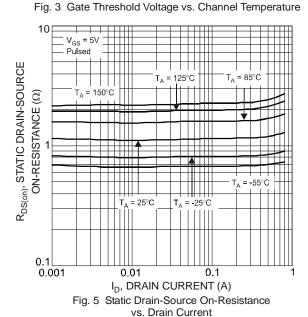
Notes:

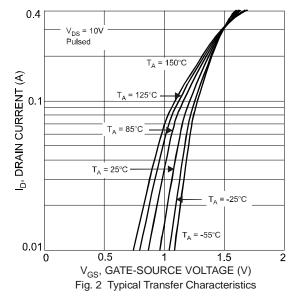
- Device mounted on FR-4 PCB.
- No purposefully added lead. Halogen and Antimony Free
- Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Short duration pulse test used to minimize self-heating effect.











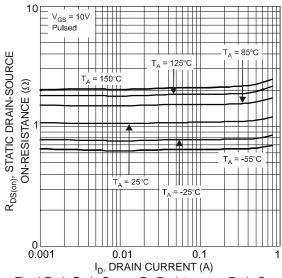
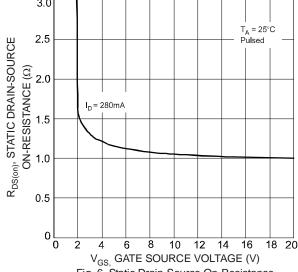


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current





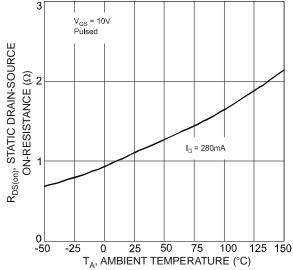


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

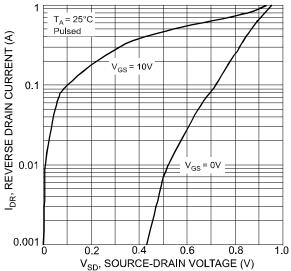
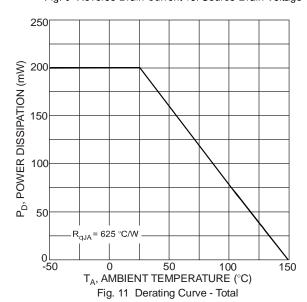


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



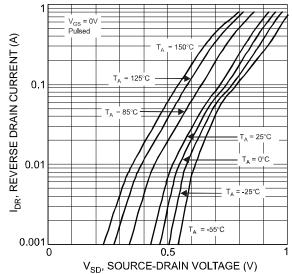


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

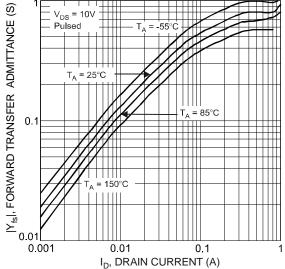


Fig.10 Forward Transfer Admittance vs. Drain Current

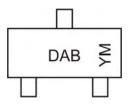


## Ordering Information (Note 6)

Part Number	Case	Packaging		
DMN5L06WK-7	SOT-323	3000/Tape & Reel		

Notes:  $6. \ For packaging \ details, go \ to \ our \ website \ at \ http://www.diodes.com/datasheets/ap02007.pdf.$ 

## **Marking Information**

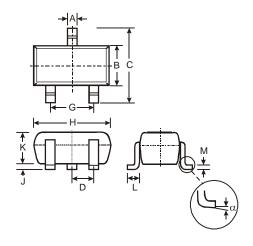


DAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

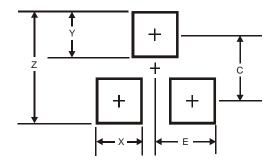
Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	V	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

# **Package Outline Dimensions**



SOT-323						
Dim	Min	Max	Тур			
Α	0.25	0.40	0.30			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D	-	-	0.65			
G	1.20 1.40		1.30			
Н	1.80	2.20	2.15			
J	0.0	0.10	0.05			
K	0.90	1.00	1.00			
L	0.25	0.40	0.30			
M	0.10	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Υ	0.9
С	1.9
E	1.0



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